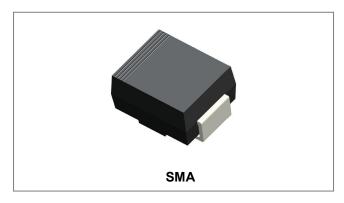






## **SL36A SCHOTTKY RECTIFIER**



#### **Features**

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters,
   Free Wheeling, and Polarity Protection Applications
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

#### **Circuit Diagram**



#### **Applications**

- · Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

## **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{RWM} \ \end{array}$	-	60	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @T <sub>c</sub> =105°C, rectangular wave form	3	А
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse, T <sub>c</sub> = 25 °C	70	А

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 3A, Pulse, T <sub>J</sub> = 25 °C	0.50	0.58	V
	V <sub>F2</sub>	@ 3A, Pulse, T <sub>J</sub> = 125℃	0.42	0.50	V
Reverse Current*	I <sub>R1</sub>	$@V_R = \text{rated } V_{R,} T_J = 25^{\circ}C$	0.02	1.0	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 125 ℃	14	55	mA
Junction Capacitance	Cj	@ $V_R$ = 5.0 V, Tc=25°C $f_{SIG}$ = 1MHz	170	250	pF
Series Inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

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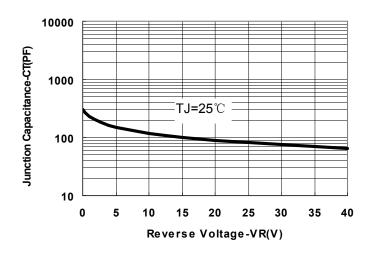




### **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +125	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +125	°C
Typical Thermal Resistance Junction to Case	R <sub>0</sub> JC	-	8	°C/W
Approximate Weight	wt	-	0.06	g

# **Ratings and Characteristics Curves**



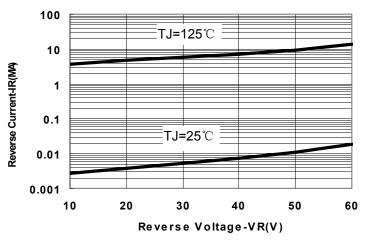


Fig.1-Typical Junction Capacitance

**Fig.2-Typical Reverse Characteristics** 

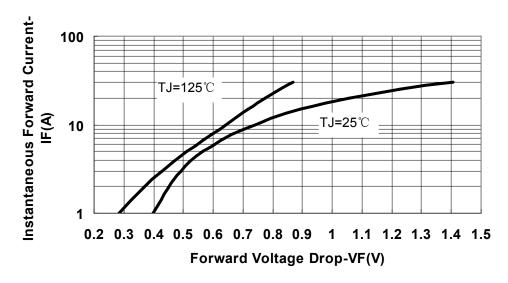


Fig.3-Typical Instantaneous Forward Voltage Characteristics

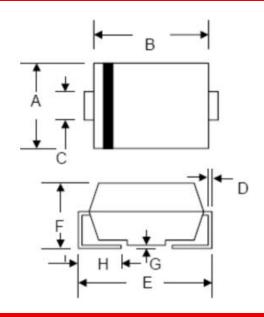
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#### **Mechanical Dimensions SMA**



SYMBOL	Millimeters		Inches		
STIVIBUL	Min.	Max.	Min.	Max.	
А	2.40	2.84	0.094	0.112	
В	3.99	4.75	0.157	0.187	
С	1.05	1.70	0.041	0.067	
D	0.15	0.51	0.006	0.020	
Е	4.80	5.66	0.189	0.223	
F	1.90	2.95	0.075	0.116	
G	0.05	0.203	0.002	0.008	
Н	0.76	1.52	0.030	0.600	

## **Ordering Information**

Device	Package	Shipping
SL36A	SMA (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

## **Marking Diagram**



Where XXXXX is YYWWL

 SL
 = Device Type

 3
 = Forward Current (3A)

 6
 = Reverse Voltage (60V)

 A
 = Package type

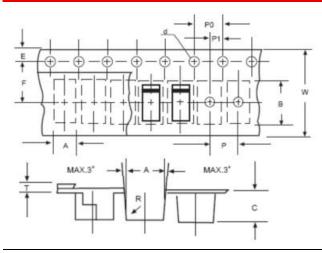
 YY
 = Year

 WW
 = Week

 L
 = Lot Number

**Cautions:** Molding resin Epoxy resin UL:94V-0

## **Carrier Tape Specification SMA**



OVMDOL	Millimeters		
SYMBOL	Min.	Max.	
Α	2.97	3.17	
В	5.70	5.90	
С	2.32	2.52	
d	1.40	1.60	
E	1.40	1.60	
F	5.60	5.70	
Р	3.90	4.10	
P0	3.90	4.10	
P1	1.90	2.10	
Т	0.25	0.35	
W	11.80	12.20	

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